EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"20050247985"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:53
S3	21739	high adj dielectric adj constant	US-PGPUB; USPAT	OR	ON	2007/05/08 14:59
S4	2218	gate and (gate near insulat $3) and (Hfsi Zr)	US-PGPUB; USPAT	OR	ON	2007/06/02 17:24
S5	710	S3 and S4	US-PGPUB; USPAT	OR	ON	2007/05/08 15:07
S6	174665	gate and silicon oxide and depth and distribut$3 and ((gate near insulat$3) near (Zr Hf Ta Al Ti Nb Sc Y La Ce Pr Nd Sm Eu Gd Tb Dy Ho Er Tm Yb Lu))	US-PGPUB; USPAT	OR	ON	2007/05/08 15:07
S7	2075	S6 and S4	US-PGPUB; USPAT	OR	ON	2007/05/08 15:07
S8	204	S5 and @ad<"20020619"	US-PGPUB; USPAT	OR	ON	2007/05/08 15:08
S13	569	(tan hfo si) adj mosfet	US-PGPUB; USPAT	OR	ON	2007/06/02 17:38
S14	310	S13 and @ad<"20020627"	US-PGPUB; USPAT	OR	ON	2007/06/02 17:30
S15	0	(tan hfo) adj mosfet	US-PGPUB; USPAT	OR	ON	2007/06/02 17:38
S16	21	(tan hfo) near2 mosfet	US-PGPUB; USPAT	OR	ON	2007/06/02 17:42
S17	20	(hag-ju near cho).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 17:47
S18	14	("20020104481" | "5316982" | "5668021" | "5668054" | "6153519" | "6168991" | "6203613" | "6204204" | "6221712" | "6357901" | "6492217" | "6504214" | "6537901" | "6607958").PN.	US-PGPUB; USPAT	OR	ON	2007/06/02 17:54
S19	7	"6380104"	US-PGPUB; USPAT	OR	ON	2007/06/02 23:10
S20	0	(Tanaka adj nobufumi).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 22:02
S21	0	(Tanaka near nobufumi).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 22:02

S22	148	(nobufumi).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 22:02
S23	637302	nitrogen	US-PGPUB; USPAT	OR	ON	2007/06/02 22:03
S24	17	S22 and S23	US-PGPUB; USPAT	OR	ON	2007/06/02 22:04
S25	0	(stack$3 adj gate) with (nitrogen adj concentrat $3) with (high adj dielectric adj constant) and (gate near insulat$3) and (silicon adj oxide)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:06
S26	7	(stack$3 adj gate) and (nitrogen adj concentrat $3) and (high adj dielectric adj constant) and (gate near insulat$3) and (silicon adj oxide)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:09
S27	16	(stack$3 adj gate) and (nitrogen adj concentrat $3) and (high adj dielectric adj constant)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:09
S28	38	(stack$3 near gate) and (nitrogen adj concentrat $3) and (high adj dielectric adj constant)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:22
S29	40	"5891798"	US-PGPUB; USPAT	OR	ON	2007/06/02 22:22
S30	158	Dharmarajan.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 22:59
S31	6	"6365467"	US-PGPUB; USPAT	OR	ON	2007/06/02 23:10
S32	8784	((438/197) or (438/299) or (438/585) or (438/587) or (438/588) or (438/592) or (438/652) or (438/653) or (438/654) or (438/656) or (438/657) or (438/680) or (438/684)).CCLS.	US-PGPUB; USPAT	OR	OFF	2007/06/11 10:47
S33	0	high near dielectric near3 gate near instulat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:31
S34	0	high near dielectric and gate near instulat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:41

S35	5868	(high near dielectric) and (gate near insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:41
S36	950	stack$3 near gate near electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:47
S37	47	S35 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:47
S38	1053	(257/411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/22 08:16
S39	576	(hafnium near oxynitride)	US-PGPUB; USPAT	OR	ON	2008/09/23 10:44
S40	1732595	(hafnium near oxynitride) near$2 (gate near (insulat $3 dielectric))	US-PGPUB; USPAT	OR	ON	2008/09/23 10:44
S41	23	(hafnium near oxynitride) near2 (gate near (insulat $3 dielectric))	US-PGPUB; USPAT	OR	ON	2008/09/23 10:44
S42	1	"20050263754"	US-PGPUB; USPAT	OR	ON	2008/09/24 11:38
S43	5702	porous near silicon	US-PGPUB; USPAT	OR	ON	2008/09/24 12:08
S44	3073	porous near silicon	USPAT	OR	ON	2008/09/24 12:08
S45	27834	sony.as.	USPAT	OR	ON	2008/09/24 12:09
S46	27	S45 and S44	USPAT	OR	ON	2008/09/24 12:09
S47	892	S44 and (sic 3c-sic (silicon near carbide))	USPAT	OR	ON	2008/09/24 12:15
S48	1	S47 and (single near cyrstal)	USPAT	OR	ON	2008/09/24 12:15
S49	14	("4090851" | "4213940" | "4264565" | "4298629" | "4312923" | "4346068" | "4368180").PN. OR ("4515755").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/09/24 12:16
S50	11	(single near cyrstal) and (sic 3c-sic (silicon near carbide))	USPAT	OR	ON	2008/09/24 12:17

S51	261	S47 and (single near crystal)	USPAT	OR	ON	2008/09/24 12:17
S52	1705	(single near crystal) with (sic 3c-sic (silicon near carbide))	USPAT	OR	ON	2008/09/24 12:19
S53	2623	(single near crystal) same (sic 3c-sic (silicon near carbide))	USPAT	OR	ON	2008/09/24 12:19
S54	61	S47 and S52	USPAT	OR	ON	2008/09/24 12:19
S55	94	S47 and S53	USPAT	OR	ON	2008/09/24 12:19
S56	3073	porous near silicon	USPAT	OR	ON	2008/09/24 15:22
S57	892	S56 and (sic 3c-sic (silicon near carbide))	USPAT	OR	ON	2008/09/24 15:22
S58	0	S57 and (cubic near boron near phosphate)	USPAT	OR	ON	2008/09/24 15:31
S59	9	S57 and (boron near phosphate)	USPAT	OR	ON	2008/09/24 15:31
S60	21	S57 and ((boron near phosphate) c-bp bp)	USPAT	OR	ON	2008/09/24 15:32
S61	0	ep1298234	US-PGPUB; USPAT	OR	ON	2008/09/24 15:41
S62	0	ep1298234	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 15:41
S63	2	ep near "1298234"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 15:41
S64	2	"20030056718"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 15:41
S65	12	"5588994"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 15:46

S66	2	S65 and boron	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 15:47
S67	32	c-BP	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 15:50
S68	15	"6844604"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/24 19:44

9/26/2008 12:35:57 PM
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